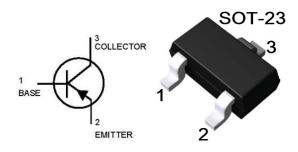
2SA1036K
TRANSISTOR
PNP GENERAL PURPOSE TRANSISTOR

## **DESCRIPTION**

## PIN DESCRIPTION

The 2SA1036K is available in SOT-23 packages.



### ORDERING INFORMATION

Package Type	Part Number	
SOT-23	2SA1036K	
Note	e SPQ: 3,000pcs/Tube	
AiT provides all RoHS products		

Din	PIN	
Pin	DESCRIPTION	
1	Base	
2	Emitter	
3	Collector	

#### ABSOLUTE MAXIMUM RATINGS

V <sub>CBO</sub> , Collector-Base Voltage	-40V
V <sub>CEO</sub> , Collector-Emitter Voltage	-25V
V <sub>EBO</sub> , Emitter-Base Voltage	-5.0V
Ic, Collector Current -Continuous	-500mA

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### THERMAL CHARACTERISTICS

P <sub>D</sub> , Total Dissipation FR-5 Board <sup>(1)</sup> T <sub>A</sub> =25°C	225mW		
Derate above 25°C	1.8mW/°C		
R <sub>0</sub> JA , Thermal Resistance, Junction to Ambient	556°C/W		
P <sub>D</sub> , Alumina Substrate <sup>(2)</sup> T <sub>A</sub> =25°C	300mW		
Derate above 25°C	1.8 mW/°C		
R <sub>0JA</sub> , Thermal Resistance, Junction to Ambient	417°C/W		
T <sub>J</sub> , Junction Temperature	150°C		
T <sub>STG</sub> , Storage Temperature	-55°C~+150°C		

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# **ELECTRICAL CHARACTERISTICS**

T<sub>A</sub> = 25°C, unless otherwise noted

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Off Characteristics						
Collector-Emitter Breakdown Voltage	V <sub>CEO</sub>	I <sub>C</sub> = -1.0mA, I <sub>B</sub> =0	-25	-	-	V
Collector-Base Breakdown Voltage	$V_{CBO}$	I <sub>C</sub> = -0.1mA, I <sub>E</sub> =0	-40	-	-	V
Emitter-Base Breakdown Voltage	V <sub>EBO</sub>	I <sub>E</sub> = -0.1mA, I <sub>C</sub> =0	-5.0	-	-	V
Base Cutoff Current	I <sub>BEV</sub>	V <sub>CE</sub> = -35V, V <sub>EB</sub> = -0.4V	-	-	-0.1	μA
Collector Cutoff Current	ICEX	V <sub>CE</sub> = -35V,V <sub>EB</sub> = -0.4V	-	-	-0.1	μA
On Characteristics						
		I <sub>C</sub> = -0.1 mA, V <sub>CE</sub> = -1.0V	30	ı	-	
		I <sub>C</sub> = -1.0 mA, V <sub>CE</sub> = -1.0V	60	1	-	
DC Current Gain	hee	I <sub>C</sub> = -10 mA, V <sub>CE</sub> = -1.0V	100	1	-	_
DC Current Gain	h <sub>FE</sub>	$I_{C}$ = -150 mA, $V_{CE}$ = -2.0 $V^{(3)}$	180	-	390	
		$I_C$ = -500 mA, $V_{CE}$ = -2.0 $V^{(3)}$	20	1	-	
Collector-Emitter Saturation		I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA	-	-	-0.4	,,
Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA	-	-	-0.75	V
5 6	V <sub>BE(sat)</sub>	I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA	-0.75	-	-0.95	V
Base-Emitter Saturation Voltage		I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA	-	1	-1.3	
Small-Signal Characteristics						
Current-Gain-Bandwidth Product	fτ	I <sub>C</sub> = -20mA V <sub>CE</sub> = -10V, f=100MHz	200	-	-	MHz
Collector-Base Capacitance	Ссв	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f=1.0MHz	-	-	8.5	pF
Emitter-Base Capacitance	Сев	V <sub>CB</sub> = -0.5V, I <sub>c</sub> =0, f=1.0MHz	-	ı	30	pF
Input Impedance	HIE	V <sub>CE</sub> = -10V, I <sub>c</sub> =-1.0 mA, f=1.0MHz	1.5	-	15	kΩ
Voltage Feedback Ratio	H <sub>RE</sub>		0.1	-	8.0	X10 <sup>-4</sup>
Small-Signal Current Gain	H <sub>FE</sub>		60	-	500	-
Switching Characteristics	•				1	1
Delay Time	t <sub>d</sub>	V <sub>CC</sub> = -30V, V <sub>EB</sub> = -2.0V,	-	-	15	-
Rise Time	<b>t</b> d	I <sub>C</sub> = -150mA, I <sub>B1</sub> = -15mA	-	-	20	ns
Storage Time	ts	V <sub>CC</sub> = -30V, I <sub>C</sub> = -150mA,	-	-	225	ns
Otorage Time						

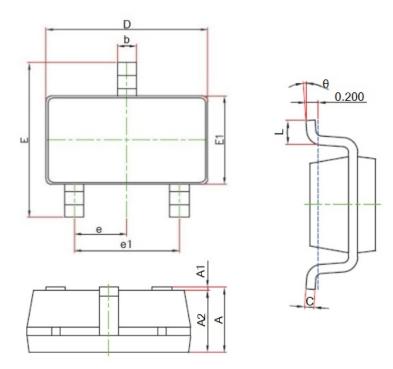
<sup>(1)</sup> FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

<sup>(2)</sup> Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

<sup>(3)</sup> Pulse Test Pulse Width ≤300us; Duty Cycle ≤2.0%.

# PACKAGE INFORMATION

Dimension in SOT-23 (Unit: mm)



Cumbal	MILLIMETERS			
Symbol	Min.	Max.		
Α	1.050	1.250		
A1	0.000	0.100		
A2	1.050	1.150		
b	0.300	0.500		
С	0.100	0.200		
D	2.820	3.020		
E1	1.500	1.700		
Е	2.650	2.950		
е	0.950(BSC)			
e1	1.800	2.000		
L	0.300	0.600		
θ	0°	8°		

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